

Taizoh Sadoh

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

191 papers	2,633 citations	29 h-index	42 g-index
236 ext. papers	2,844 ext. citations	2.2 avg, IF	4.8 L-index

#	Paper	IF	Citations
191	Electrical properties of poly-Ge on glass substrate grown by two-step solid-phase crystallization. <i>Solid-State Electronics</i> , 2009 , 53, 1159-1164	1.7	116
190	Electrical injection and detection of spin-polarized electrons in silicon through an Fe ₃ Si/Si Schottky tunnel barrier. <i>Applied Physics Letters</i> , 2009 , 94, 182105	3.4	113
189	Orientation-controlled Si thin films on insulating substrates by Al-induced crystallization combined with interfacial-oxide layer modulation. <i>Applied Physics Letters</i> , 2009 , 95, 132103	3.4	103
188	Low-temperature formation (. <i>Applied Physics Letters</i> , 2006 , 89, 192114	3.4	85
187	Epitaxial ferromagnetic Fe ₃ SiBi(111) structures with high-quality heterointerfaces. <i>Applied Physics Letters</i> , 2008 , 93, 132117	3.4	79
186	High-quality single-crystal Ge stripes on quartz substrate by rapid-melting-growth. <i>Applied Physics Letters</i> , 2009 , 95, 022115	3.4	67
185	Effect of atomically controlled interfaces on Fermi-level pinning at metal/Ge interfaces. <i>Applied Physics Letters</i> , 2010 , 96, 162104	3.4	64
184	Temperature dependent metal-induced lateral crystallization of amorphous SiGe on insulating substrate. <i>Applied Physics Letters</i> , 2006 , 89, 182120	3.4	64
183	High carrier mobility in orientation-controlled large-grain (100) Ge directly formed on flexible plastic by nucleation-controlled gold-induced-crystallization. <i>Applied Physics Letters</i> , 2014 , 104, 252110	3.4	61
182	Nucleation-controlled gold-induced-crystallization for selective formation of Ge(100) and (111) on insulator at low-temperature (~250 °C). <i>Applied Physics Letters</i> , 2013 , 103, 082102	3.4	60
181	Ni-imprint induced solid-phase crystallization in Si _{1-x} Ge _x (x: 0.1) on insulator. <i>Applied Physics Letters</i> , 2007 , 91, 042111	3.4	56
180	Electrical and structural properties of poly-SiGe film formed by pulsed-laser annealing. <i>Journal of Applied Physics</i> , 2004 , 95, 6457-6461	2.5	53
179	Atomically controlled molecular beam epitaxy of ferromagnetic silicide Fe ₃ Si on Ge. <i>Applied Physics Letters</i> , 2006 , 89, 182511	3.4	46
178	Enhanced Interfacial-Nucleation in Al-Induced Crystallization for (111) Oriented Si _{1-x} Ge _x (0.1) Films on Insulating Substrates. <i>ECS Journal of Solid State Science and Technology</i> , 2012 , 1, P144-P147	2	44
177	Chip-size formation of high-mobility Ge strips on SiN films by cooling rate controlled rapid-melting growth. <i>Applied Physics Letters</i> , 2011 , 99, 032103	3.4	42
176	Deep levels of vanadium and vanadium-hydrogen complex in silicon. <i>Journal of Applied Physics</i> , 1992 , 72, 520-524	2.5	39
175	Comprehensive study of Al-induced layer-exchange growth for orientation-controlled Si crystals on SiO ₂ substrates. <i>Journal of Applied Physics</i> , 2014 , 116, 173510	2.5	37

174	Magnetic properties of epitaxially grown Fe ₃ Si/Ge(111) layers with atomically flat heterointerfaces. <i>Journal of Applied Physics</i> , 2009 , 105, 07B102	2.5	37
173	Low-temperature molecular beam epitaxy of a ferromagnetic full-Heusler alloy Fe ₂ MnSi on Ge(111). <i>Applied Physics Letters</i> , 2008 , 93, 112108	3.4	36
172	Source/Drain Engineering Using Atomically Controlled Heterojunctions for Next-Generation SiGe Transistor Applications. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 010101	1.4	34
171	Deep level of iron-hydrogen complex in silicon. <i>Journal of Applied Physics</i> , 1997 , 82, 3828-3831	2.5	34
170	Ge-fraction-dependent metal-induced lateral crystallization of amorphous-Si _{1-x} Ge _x (0 ≤ x ≤ 1) on SiO ₂ . <i>Applied Physics Letters</i> , 2003 , 82, 2148-2150	3.4	32
169	Deep levels of chromium-hydrogen complexes in silicon. <i>Journal of Applied Physics</i> , 1994 , 75, 3978-3981	2.5	32
168	Ion-beam modification of TiO ₂ film to multilayered photocatalyst. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1999 , 148, 758-761	1.2	31
167	High carrier mobility of Sn-doped polycrystalline-Ge films on insulators by thickness-dependent low-temperature solid-phase crystallization. <i>Applied Physics Letters</i> , 2016 , 109, 232106	3.4	31
166	Interfacial-Oxide Layer Controlled Al-Induced Crystallization of Si _{1-x} Ge _x (x: 0 ≤ x ≤ 1) on Insulating Substrate. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 03B002	1.4	29
165	Open-gated pH sensor fabricated on an undoped-AlGaIn/GaN HEMT structure. <i>Sensors</i> , 2011 , 11, 3067-773.8	3.8	29
164	Axial orientation of molecular-beam-epitaxy-grown Fe ₃ Si/Ge hybrid structures and its degradation. <i>Applied Physics Letters</i> , 2007 , 91, 171910	3.4	29
163	Diffusion of vanadium in silicon. <i>Applied Physics Letters</i> , 1991 , 58, 1653-1655	3.4	29
162	Low-Temperature (~ 250°C) Cu-Induced Lateral Crystallization of Amorphous Ge on Insulator. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H274		27
161	Al-Induced oriented-crystallization of Si films on quartz and its application to epitaxial template for Ge growth. <i>Solid-State Electronics</i> , 2011 , 60, 7-12	1.7	26
160	Single-crystalline laterally graded GeSn on insulator structures by segregation controlled rapid-melting growth. <i>Applied Physics Letters</i> , 2012 , 101, 091905	3.4	26
159	Au-Induced Low-Temperature (~250°C) Crystallization of Si on Insulator Through Layer-Exchange Process. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H232		25
158	Ultra-high-speed lateral solid phase crystallization of GeSn on insulator combined with Sn-melting-induced seeding. <i>Applied Physics Letters</i> , 2014 , 105, 202112	3.4	24
157	Enhanced crystal nucleation in a-SiGe/SiO ₂ by ion-irradiation assisted annealing. <i>Applied Surface Science</i> , 2004 , 224, 231-234	6.7	24

156	Ion-beam stimulated solid-phase crystallization of amorphous Si on SiO ₂ . <i>Thin Solid Films</i> , 2001 , 383, 104-106	2.2	23
155	Epitaxial Growth of Ferromagnetic Silicide Fe ₃ Si on Si(111) Substrate. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 3598-3600	1.4	22
154	Defect-free single-crystal Ge island arrays on insulator by rapid-melting-growth combined with seed-positioning technique. <i>Applied Physics Letters</i> , 2009 , 95, 112107	3.4	21
153	Hybrid-orientation Ge-on-insulator structures on (100) Si platform by Si micro-seed formation combined with rapid-melting growth. <i>Applied Physics Letters</i> , 2012 , 100, 172107	3.4	21
152	Low temperature (~250°C) layer exchange crystallization of Si _{1-x} Ge _x (x=10) on insulator for advanced flexible devices. <i>Thin Solid Films</i> , 2012 , 520, 3293-3295	2.2	20
151	Novel growth techniques of group-IV based semiconductors on insulator for next-generation electronics. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 05DA06	1.4	19
150	Indentation-induced low-temperature solid-phase crystallization of Si _{1-x} Ge _x (x=0.1) on insulator. <i>Applied Physics Letters</i> , 2009 , 94, 192106	3.4	19
149	Single-crystalline (100) Ge networks on insulators by rapid-melting growth along hexagonal mesh-pattern. <i>Applied Physics Letters</i> , 2011 , 98, 042101	3.4	18
148	Pulsed laser crystallization of silicon-germanium films. <i>Thin Solid Films</i> , 2005 , 487, 67-71	2.2	18
147	Growth-rate-dependent laterally graded SiGe profiles on insulator by cooling-rate controlled rapid-melting-growth. <i>Applied Physics Letters</i> , 2012 , 101, 241904	3.4	17
146	(100) Orientation-Controlled Ge Giant-Stripes on Insulating Substrates by Rapid-Melting Growth Combined with Si Micro-Seed Technique. <i>Applied Physics Express</i> , 2010 , 3, 075603	2.4	17
145	Au-induced lateral crystallization of a-Si _{1-x} Ge _x (x: 0.1) at low temperature. <i>Thin Solid Films</i> , 2006 , 508, 44-47	2.2	17
144	High Quality Single-Crystalline Ge-Rich SiGe on Insulator Structures by Si-Doping Controlled Rapid Melting Growth. <i>Applied Physics Express</i> , 2010 , 3, 031301	2.4	16
143	Defect-free Ge-on-insulator with (100), (110), and (111) orientations by growth-direction-selected rapid-melting growth. <i>Applied Physics Letters</i> , 2010 , 97, 152101	3.4	16
142	Epitaxial growth of a full-Heusler alloy Co ₂ FeSi on silicon by low-temperature molecular beam epitaxy. <i>Thin Solid Films</i> , 2010 , 518, S278-S280	2.2	16
141	Highly strain-relaxed ultrathin SiGe-on-insulator structure by Ge condensation process combined with H ⁺ irradiation and postannealing. <i>Applied Physics Letters</i> , 2006 , 88, 142105	3.4	16
140	Low-temperature solid-phase crystallization of a-Si _{1-x} Ge _x on SiO ₂ by ion-beam stimulation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002 , 89, 336-340	3.1	16
139	Source/Drain Engineering Using Atomically Controlled Heterojunctions for Next-Generation SiGe Transistor Applications. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 010101	1.4	16

138	Low-temperature (~180 °C) position-controlled lateral solid-phase crystallization of GeSn with laser-anneal seeding. <i>Applied Physics Letters</i> , 2015 , 107, 262106	3.4	15
137	Growth kinetics of CoSi formed by ion beam irradiation at room temperature. <i>Journal of Applied Physics</i> , 1997 , 82, 5480-5483	2.5	15
136	Behavior of radiation-induced defects and amorphization in silicon crystal. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1997 , 121, 299-301	1.2	15
135	Ge-Channel Thin-Film Transistor with Schottky Source/Drain Fabricated by Low-Temperature Processing. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 1250-1253	1.4	15
134	Metal-Induced Solid-Phase Crystallization of Amorphous SiGe Films on Insulator. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 1933-1936	1.4	15
133	Electrical and thermal properties of structurally metastable iron-boron pairs in silicon. <i>Physical Review B</i> , 1994 , 49, 16983-16993	3.3	15
132	Low temperature formation of multi-layered structures of ferromagnetic silicide Fe ₃ Si and Ge. <i>Applied Surface Science</i> , 2008 , 254, 6215-6217	6.7	14
131	Modified metal-induced lateral crystallization using amorphous GeBi layered structure. <i>Applied Physics Letters</i> , 2004 , 85, 899-901	3.4	14
130	(111)-oriented large-grain (80 μm) Ge crystals directly formed on flexible plastic substrate by gold-induced layer-exchange crystallization. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 020302	1.4	13
129	High-quality formation of multiply stacked SiGe-on-insulator structures by temperature-modulated successive rapid-melting-growth. <i>Applied Physics Letters</i> , 2013 , 102, 092102	3.4	13
128	Enhanced stress relaxation in ultrathin SiGe-on-insulator by H ⁺ -implantation-assisted oxidation. <i>Applied Physics Letters</i> , 2005 , 86, 211901	3.4	13
127	Pulse number controlled laser annealing for GeSn on insulator structure with high substitutional Sn concentration. <i>Applied Physics Letters</i> , 2016 , 108, 262105	3.4	13
126	Quasi-single crystal SiGe on insulator by Au-induced crystallization for flexible electronics. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 03CB01	1.4	12
125	Low-temperature crystallization of amorphous silicon and amorphous germanium by soft X-ray irradiation. <i>Thin Solid Films</i> , 2013 , 534, 334-340	2.2	12
124	Mesh-shape-and-size controlled rapid-melting growth for the formation of single-crystalline (100), (110), and (111) Ge networks on insulators. <i>Applied Physics Letters</i> , 2011 , 98, 182107	3.4	12
123	Giant growth of single crystalline Ge on insulator by seeding lateral liquid-phase epitaxy. <i>Thin Solid Films</i> , 2010 , 518, S170-S173	2.2	12
122	Effects of ion irradiation on silicon oxidation in electron cyclotron resonance argon and oxygen mixed plasma. <i>Journal of Applied Physics</i> , 2000 , 88, 1664-1669	2.5	12
121	Selective-mapping of uniaxial and biaxial strains in Si-on-insulator microstructures by polarized microprobe Raman spectroscopy. <i>Applied Physics Letters</i> , 2011 , 98, 012110	3.4	11

120	Influence of substrate orientation on low-temperature epitaxial growth of ferromagnetic silicide Fe ₃ Si on Si. <i>Thin Solid Films</i> , 2007 , 515, 8250-8253	2.2	11
119	Ge fraction dependent improved thermal stability of in situ doped boron in polycrystalline Si _{1-x} Ge _x (0 ≤ x ≤ 0.5) films on SiON. <i>Journal of Applied Physics</i> , 2005 , 97, 054909	2.5	11
118	Crystallization of Electrodeposited Germanium Thin Film on Silicon (100). <i>Materials</i> , 2013 , 6, 5047-5057	3.5	10
117	OPTICAL AND ELECTRONIC PROPERTIES OF M ₂ Si (M = Mg, Ca, Sr) GROWN BY REACTIVE DEPOSITION TECHNIQUE. <i>International Journal of Modern Physics B</i> , 2010 , 24, 3693-3699	1.1	10
116	Molecular beam epitaxial growth of ferromagnetic Heusler alloys for group-IV semiconductor spintronic devices. <i>Thin Solid Films</i> , 2010 , 518, S273-S277	2.2	10
115	Electric-Field-Assisted Metal-Induced Lateral Crystallization of Amorphous SiGe on SiO ₂ . <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 4351-4354	1.4	10
114	Enhanced mobility of Sn-doped Ge thin-films (50 nm) on insulator for fully depleted transistors by nucleation-controlled solid-phase crystallization. <i>Applied Physics Letters</i> , 2019 , 115, 042101	3.4	9
113	Large-grain SiGe-on-insulator with uniform Si concentration by segregation-free rapid-melting growth. <i>Applied Physics Letters</i> , 2014 , 105, 102106	3.4	9
112	Al-induced low-temperature crystallization of Si _{1-x} Ge _x (0 ≤ x ≤ 1). <i>Thin Solid Films</i> , 2010 , 518, S174-S178	2.2	9
111	Etching characteristics of SiO ₂ irradiated with focused ion beam. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003 , 206, 478-481	1.2	9
110	Magneto-optical properties of iron based Heusler alloy epitaxial films on Ge(111). <i>Physics Procedia</i> , 2011 , 11, 200-203		8
109	Thickness-dependent stress-relaxation in thin SGOI structures and its improvement. <i>Thin Solid Films</i> , 2006 , 508, 247-250	2.2	8
108	Nucleation Control in Solid-Phase Crystallization of a-Si/SiO ₂ by Local Ge Insertion. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 1901-1904	1.4	8
107	Ge-dependent morphological change in poly-SiGe formed by Ni-mediated crystallization. <i>Applied Surface Science</i> , 2004 , 224, 227-230	6.7	8
106	Ion-beam irradiation effect on solid-phase growth of FeFeSi ₂ . <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 16, 505-508	3	8
105	400 °C Formation of poly-SiGe on SiO ₂ by Au-induced lateral crystallization. <i>Materials Science in Semiconductor Processing</i> , 2005 , 8, 79-82	4.3	7
104	Low-Temperature Formation of Poly-Si _{1-x} Ge _x (x: 0 ≤ x ≤ 1) on SiO ₂ by Au-Mediated Lateral Crystallization. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 2405-2408	1.4	7
103	Hole traps of metastable iron-boron pairs in silicon. <i>Journal of Applied Physics</i> , 1993 , 73, 2803-2808	2.5	7

102	Giant-Lateral-Growth of SiGe Stripes on Insulating-Substrate by Self-Organized-Seeding and Rapid-Melting-Growth in Solid-Liquid Coexisting Region. <i>ECS Solid State Letters</i> , 2014 , 3, P61-P64		6
101	Epitaxial-Template Structure Utilizing Ge-on-Insulator Stripe Arrays with Nanospacing for Advanced Heterogeneous Integration on Si Platform. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 06FF04	1.4	6
100	Nucleation-Controlled Metal-Induced Lateral Crystallization of Amorphous Si _{1-x} Ge _x with Whole Ge Fraction on Insulator. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 1876-1879	1.4	6
99	Influences of Si pillar geometry on SiN-stressor induced local strain. <i>Applied Surface Science</i> , 2008 , 254, 6226-6228	6.7	6
98	Atomically controlled hetero-epitaxy of Fe ₃ Si/SiGe for spintronics application. <i>Thin Solid Films</i> , 2008 , 517, 181-183	2.2	6
97	Characterization of metal-induced lateral crystallization of amorphous SiGe on insulating film. <i>Thin Solid Films</i> , 2006 , 508, 57-60	2.2	6
96	Solid-phase crystallization of FeSi ₂ thin film in Fe/Si structure. <i>Thin Solid Films</i> , 2004 , 461, 68-71	2.2	6
95	High Sn-concentration (~8%) GeSn by low-temperature (~150°C) solid-phase epitaxy of a-GeSn/c-Ge. <i>Thin Solid Films</i> , 2016 , 602, 20-23	2.2	5
94	Thickness Dependent Solid-Phase Crystallization of Amorphous GeSn on Insulating Substrates at Low Temperatures (. <i>ECS Solid State Letters</i> , 2015 , 4, P95-P97		5
93	The Effects of Annealing Temperatures on Composition and Strain in SiGe Obtained by Melting Growth of Electrodeposited Ge on Si (100). <i>Materials</i> , 2014 , 7, 1409-1421	3.5	5
92	Nano-lithography free formation of high density Ge-on-insulator network for epitaxial template. <i>Applied Physics Letters</i> , 2012 , 100, 092111	3.4	5
91	Laterally-Graded Doping into Ge-on-Insulator by Combination of Ion-Implantation and Rapid-Melting Growth. <i>ECS Solid State Letters</i> , 2013 , 2, P58-P60		5
90	Microscopic studies of metal-induced lateral crystallization in SiGe. <i>Applied Physics Letters</i> , 2010 , 96, 182301	3.4	5
89	High-Hole-Mobility Single-Crystalline Ge Thin Films Formed on Insulating Substrates by SiGe Mixing-Triggered Directional Melting Growth. <i>Japanese Journal of Applied Physics</i> , 2010 , 49, 04DA08	1.4	5
88	SiGe-Mixing-Triggered Rapid-Melting-Growth of High-Mobility Ge-On-Insulator. <i>Key Engineering Materials</i> , 2011 , 470, 8-13	0.4	5
87	Comprehensive study of low temperature (. <i>Thin Solid Films</i> , 2008 , 517, 251-253	2.2	5
86	Solid-phase crystallization of high-quality Si films on SiO ₂ by local Ge-insertion. <i>Thin Solid Films</i> , 2004 , 451-452, 489-492	2.2	5
85	Ge-enhanced MILC velocity in a-Ge/a-Si/SiO ₂ layered structure. <i>Materials Science in Semiconductor Processing</i> , 2005 , 8, 83-88	4.3	5

84	Metastable Defects of Iron-Boron Pair in Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1992 , 262, 555		5
83	Low-Temperature Formation of Large-Grain (100 nm) Ge at Controlled-Position on Insulator by Gold-Induced Crystallization Combined with Diffusion-Barrier Patterning. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P179-P182	2	4
82	Ultra-low temperature (800 °C) growth of Ge-rich SiGe by solid-liquid-coexisting annealing of a-GeSn/c-Si structures. <i>Journal of Applied Physics</i> , 2015 , 118, 095707	2.5	4
81	Ion channeling study of epitaxy of iron based Heusler alloy films on Ge(111). <i>Thin Solid Films</i> , 2011 , 519, 8461-8467	2.2	4
80	Formation of single-crystalline Ge stripes on quartz substrates by SiGe mixing-triggered liquid-phase epitaxy. <i>Thin Solid Films</i> , 2010 , 518, S179-S181	2.2	4
79	Temperature dependent epitaxial growth of ferromagnetic silicide Fe ₃ Si on Ge substrate. <i>Thin Solid Films</i> , 2008 , 517, 422-424	2.2	4
78	Low temperature epitaxial growth of Fe ₃ Si on Si(111) substrate through ultra-thin SiO ₂ films. <i>Thin Solid Films</i> , 2008 , 517, 425-427	2.2	4
77	Enhanced crystal nucleation in a-Si on SiO ₂ by local Ge doping. <i>Thin Solid Films</i> , 2004 , 464-465, 99-102	2.2	4
76	Improvement of Oxidation-Induced Ge Condensation Method by H ⁺ Implantation and Two-Step Annealing for Highly Stress-Relaxed SiGe-on-Insulator. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 2357-2360	1.4	4
75	Dose Rate Dependence of Ion-Induced-Damage in Si Evaluated by Spectroscopic Ellipsometry. <i>Solid State Phenomena</i> , 2001 , 78-79, 341-344	0.4	4
74	Thin CoSi ₂ Formation on SiO ₂ with Low-Energy Ion Irradiation. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 6117-6122	1.4	4
73	Behavior of Defects Induced by Low-Energy Ions in Silicon Films. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 7151-7155	1.4	4
72	Formation of germanium (111) on graphene on insulator by rapid melting growth for novel germanium-on-insulator structure. <i>Materials Letters</i> , 2016 , 168, 223-227	3.3	3
71	Sn-induced low-temperature (~ 150 °C) crystallization of Ge on insulator. <i>Thin Solid Films</i> , 2014 , 557, 155-158	2.5	3
70	In-depth analysis of high-quality Ge-on-insulator structure formed by rapid-melting growth. <i>Thin Solid Films</i> , 2014 , 557, 139-142	2.2	3
69	Effects of Si Layer Thickness on Solid-Phase Crystallization of Stacked Ge/Si/SiO ₂ Structures. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 03B004	1.4	3
68	Au-Catalyst Induced Low Temperature (~250 °C) Layer Exchange Crystallization for SiGe On Insulator. <i>ECS Transactions</i> , 2011 , 35, 39-42	1	3
67	Deep states in silicon on sapphire by transient-current spectroscopy. <i>Journal of Applied Physics</i> , 1997 , 82, 5262-5264	2.5	3

66	Suppression of Floating Body Effects in Polycrystalline Silicon Thin-Film Transistor by Schottky Source/Drain Structure. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 4370-4373	1.4	3
65	Enhancement of metal-induced crystallization in Ge/Si/Ni/SiO ₂ layered structure. <i>Thin Solid Films</i> , 2004 , 451-452, 324-327	2.2	3
64	Impurity conduction in ion beam synthesized α -FeSi ₂ /Si. <i>Thin Solid Films</i> , 2004 , 461, 198-201	2.2	3
63	Enhancement of bulk nucleation in α -Si _{1-x} Ge _x on SiO ₂ for low-temperature solid-phase crystallization. <i>Thin Solid Films</i> , 2003 , 427, 96-100	2.2	3
62	Large single-crystal Ge-on-insulator by thermally-assisted (~400 °C) Si-seeded-pulse-laser annealing. <i>Materials Science in Semiconductor Processing</i> , 2017 , 70, 8-11	4.3	2
61	Low-temperature (300 °C) formation of orientation-controlled large-grain (100 nm) Ge-rich SiGe on insulator by gold-induced crystallization. <i>Thin Solid Films</i> , 2016 , 602, 3-6	2.2	2
60	Enhancement of SiN-induced compressive and tensile strains in Si free-standing microstructures by modulation of SiN network structures. <i>Thin Solid Films</i> , 2012 , 520, 3276-3278	2.2	2
59	High quality, giant crystalline-Ge stripes on insulating substrate by rapid-thermal-annealing of Sn-doped amorphous-Ge in solid-liquid coexisting region. <i>AIP Advances</i> , 2015 , 5, 067112	1.5	2
58	Stress-enhancement in free-standing Si pillars through nonequilibrium dehydrogenation in SiN:H stress-liners by ultraviolet light irradiation. <i>Applied Physics Letters</i> , 2009 , 95, 262103	3.4	2
57	Position-Controlled Growth of SiGe Crystal Grains on Insulator by Indentation-Induced Solid-Phase Crystallization. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 03B007	1.4	2
56	Growth-direction-dependent characteristics of Ge-on-insulator by SiGe mixing triggered melting growth. <i>Solid-State Electronics</i> , 2011 , 60, 18-21	1.7	2
55	Dehydrogenation-Enhanced Large Strain (1.6%) in Si Pillars Covered by Si ₃ N ₄ Stress Liners. <i>Electrochemical and Solid-State Letters</i> , 2011 , 14, H174-H176		2
54	Abnormal oxidation characteristics of SiGe/Si-on-insulator structures depending on piled-up Ge fraction at SiO ₂ /SiGe interface. <i>Journal of Applied Physics</i> , 2008 , 103, 054909	2.5	2
53	Low-temperature solid-phase crystallization of amorphous SiGe films on glass by imprint technique. <i>Solid-State Electronics</i> , 2008 , 52, 1221-1224	1.7	2
52	Improved Oxidation-Induced Ge Condensation Technique Using H ⁺ Implantation and Post Annealing for Highly Stress-Relaxed Ultrathin SiGe on Insulator. <i>Japanese Journal of Applied Physics</i> , 2006 , 45, 3147-3149	1.4	2
51	Electric field-dependent Ni-mediated lateral crystallization of α -Si on SiO ₂ . <i>Thin Solid Films</i> , 2006 , 508, 40-43	2.2	2
50	Formation of α -FeSi ₂ -xGe _x by Ge-Segregation-Controlled Solid-Phase Growth of [a-Si/a-FeSiGe] _n Multilayered Structure. <i>Japanese Journal of Applied Physics</i> , 2004 , 43, 1879-1881	1.4	2
49	Directional Growth of Si Nanowires on Insulating Films by Electric-Field-Assisted Metal-Induced Lateral Crystallization. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 891, 1		2

48	Electrical passivation of B-doped Si through thin films used in VLSI fabrication. <i>Thin Solid Films</i> , 1996 , 286, 299-304	2.2	2
47	30-4: Characterization of Si Thin Films Doped by Wet-Chemical Laser Processing. <i>Digest of Technical Papers SID International Symposium</i> , 2017 , 48, 430-432	0.5	1
46	High mobility sputtered InSb film by blue laser diode annealing. <i>AIP Advances</i> , 2019 , 9, 045009	1.5	1
45	Fabrication of CMOS Invertors in Si Thin-Film-Transistors by Laser Doping Using a Chemical Solution Coating. <i>IEEE Journal of the Electron Devices Society</i> , 2020 , 8, 27-32	2.3	1
44	Nucleation-controlled low-temperature solid-phase crystallization for Sn-doped polycrystalline-Ge film on insulator with high carrier mobility ($\sim 550 \text{ cm}^2/\text{V s}$). <i>Applied Physics Letters</i> , 2018 , 112, 242103	3.4	1
43	Coherent lateral-growth of Ge over insulating film by rapid-melting-crystallization. <i>Thin Solid Films</i> , 2014 , 557, 135-138	2.2	1
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